

Amendments to the Claims:

Please amend claims 1, 3, 5-8, 10, 13-15 and 17 as shown in the following listing of claims. This listing of claims will replace all prior versions, and listings, of claims in the application.

1 1. (currently amended) A device for emitting output light, said device
2 comprising:
3 a ~~semiconductor chip light source~~ that emits first light of a first
4 peak wavelength in a 481-520 nm range; and
5 a wavelength-shifting region optically coupled to said
6 ~~semiconductor chip light source~~ to receive said first light, said wavelength-
7 shifting region including Group IIB element Selenide-based phosphor material
8 having a property to convert some of said first light to second light of a second
9 peak wavelength in a red wavelength range, said Group IIB element Selenide-
10 based phosphor material including Group IIB element Selenide activated by at
11 least one element selected from a group consisting of Copper, Chlorine, Fluorine,
12 Bromine and Silver, said first light and said second light being components of said
13 output light.

1 2. (original) The device of claim 1 wherein said Group IIB element Selenide-
2 based phosphor material of said wavelength-shifting region includes Zinc
3 Selenide.

1 3. (currently amended) The device of claim 2 wherein said Group IIB
2 element Selenide-based phosphor material of said wavelength-shifting region
3 includes said Zinc Selenide activated by ~~at least one element selected from a~~
4 ~~group consisting of Copper, Chlorine, Fluorine, Bromine and Silver.~~

1 4. (original) The device of claim 1 wherein said Group IIB element Selenide-
2 based phosphor material of said wavelength-shifting region includes Cadmium
3 Selenide.

1 5. (currently amended) The device of claim 1 wherein said semiconductor
2 chip is light source includes a light emitting diode die that can generate said first
3 light of said first peak wavelength.

1 6. (currently amended) The device of claim 1 wherein said wavelength-
2 shifting region is a part of a lamp coupled to said semiconductor chip light source.

1 7. (currently amended) The device of claim 1 wherein said wavelength-
2 shifting region is a lamp coupled to said semiconductor chip light source.

1 8. (currently amended) A device for emitting output light, said device
2 comprising:
3 a semiconductor die that emits first light of a first peak wavelength
4 in a 481-520 nm range; and
5 a phosphor-containing medium positioned to receive said first
6 light, said phosphor-containing medium including Group IIB element Selenide-
7 based phosphor material having a property to convert some of said first light to
8 second light of a second peak wavelength in a red wavelength range, said Group
9 IIB element Selenide-based phosphor material including Group IIB element
10 Selenide activated by at least one element selected from a group consisting of
11 Copper, Chlorine, Fluorine, Bromine and Silver, said first light and said second
12 light being components of said output light.

1 9. (original) The device of claim 8 wherein said Group IIB element Selenide-
2 based phosphor material of said phosphor-containing medium includes Zinc
3 Selenide.

1 10. (currently amended) The device of claim 9 wherein said Group IIB
2 element Selenide-based phosphor material of said phosphor-containing medium
3 includes said Zinc Selenide activated by at least one element selected from a
4 group consisting of Copper, Chlorine, Fluorine, Bromine and Silver.

1 11. (original) The device of claim 8 wherein said Group IIB element Selenide-
2 based phosphor material of said phosphor-containing medium includes Cadmium
3 Selenide.

1 12. (original) The device of claim 8 wherein said semiconductor die is a light
2 emitting diode die.

1 13. (currently amended) The device of claim 8 wherein said phosphor-
2 containing medium is a part of a lamp coupled to said semiconductor die ~~light~~
3 ~~source~~.

1 14. (currently amended) The device of claim 8 wherein said phosphor-
2 containing medium is a lamp coupled to said semiconductor die ~~light~~ ~~source~~.

1 15. (currently amended) A method for emitting output light, said method
2 comprising:
3 generating first light of a first peak wavelength in a 481-520 nm
4 range at a semiconductor die, including emitting said first light out of said
5 semiconductor die;
6 receiving said first light emitted out of said semiconductor die,
7 including converting some of said first light to second light of a second peak
8 wavelength in a red wavelength range using Group IIB element Selenide-based
9 phosphor material, said Group IIB element Selenide-based phosphor material
10 including Group IIB element Selenide activated by at least one element selected
11 from a group consisting of Copper, Chlorine, Fluorine, Bromine and Silver; and
12 emitting said first light and said second light as components of said
13 output light.

1 16. (original) The method of claim 15 wherein said Group IIB element
2 Selenide-based phosphor material includes Zinc Selenide.

1 17. (currently amended) The method of claim 16 wherein said Group IIB
2 element Selenide-based phosphor material includes said Zinc Selenide activated
3 by at least one element selected from a group consisting of Copper, Chlorine,
4 Fluorine, Bromine and Silver.

1 18. (original) The method of claim 15 wherein said Group IIB element
2 Selenide-based phosphor material includes Cadmium Selenide.

1 19. (original) The method of claim 15 wherein said generating includes
2 generating said first light of said first peak wavelength at a light emitting diode
3 die.

1 20. (original) The method of claim 19 wherein said light emitting diode die is
2 configured to generate said first light such that said first peak wavelength is within
3 a blue-green region of the visible light spectrum.